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## PES University, Bangalore (Established under Karnataka Act No. 16 of 2013)

**UE20EC101** 

DEC 2021: END SEMESTER ASSESSMENT- B.TECH. I/II SEMESTER

## DEC 2021: END SEMESTER ASSESSMENT- B.TECH. I/II SEMESTER UE20EC101 –Electronic Principles and Devices

Time: 180 mins Answer All Questions Max Mar			00
1.	a	Give the Difference between the following.	6M
		(i) Avalanche Breakdown and Zener Breakdown	
	2.5	(ii) Static Resistance and Dynamic Resistance	
		(iii) Ideal diode and Practical diode	
	b	Solve the following using second approximation for a diode.	8M
		(i) Determine Vo and I <sub>D</sub>	
		+8 V 1.2 kΩ V <sub>o</sub>	
		$I_D \downarrow $ $\stackrel{\checkmark}{\bullet}$ Si $\stackrel{\checkmark}{\bullet}$ $\stackrel{\circ}{\bullet}$ $$	
		(ii) Determine I <sub>1</sub> , I <sub>2</sub> and V <sub>1</sub> for the circuit shown in the Figure below	
		I <sub>1</sub> Si	
		$E = 18V  D_2  \text{Si}  \begin{cases} 12 \\ 2.2K\Omega \end{cases}$	
		-V <sub>1</sub> + -V <sub>2</sub> + -V <sub>1</sub> + -V <sub>2</sub> + -V <sub>1</sub> + -V <sub>2</sub>	
	С	Using Shockley's equation, Find the diode current $I_d$ for a silicon Diode, if the applied voltage $V_D$ =0.71 and Reverse Saturation Current is 4 x 10 <sup>-12</sup> A at a temp of 30 <sup>0</sup> C. Consider ( $\eta$ =1).	6M
2.	a		6M
	b	Derive the expression for I <sub>dc</sub> , I <sub>rms</sub> and hence find the Efficiency for Full wave Rectifier	8M
1	С	Determine the range of values of Vi that will maintain the Zener diode in the "on" state.	6M

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		$V_{I} = 18V I_{IZ}$ $V_{IZM} = 60 \text{ mA}$ $V_{IZ} = 18V I_{IZM} = 60 \text{ mA}$ $V_{IZM} = 60 \text{ mA}$	
3.	a	Find the Min-terms for the function $F = AB+BC+AC$ by Converting into canonical SOP. Realize the SOP using Basic Gates.	6 M
	b	Using Truth Table for Full Adder Realize Full Adder using (i) XOR gates (ii) Basic Gates.	8 M
	С	Discuss the following Sequential Circuits using Circuit diagram and Characteristic Table  (i) JK Flip Flop  (ii) 3 bit Asynchronous up-counter	6 M
4.	a	With a neat diagram explain the Input and output V-I characteristics of NPN BJT Common Emitter Characteristics.	6M
	b	Derive the relation between $\alpha$ and $\beta$ and Find the value of $I_B$ , $\alpha$ and $\beta$ if $I_E=1.2mA$ and $I_C=1.15mA$ .	8M
	С	Explain Cellular Communication with a neat diagram.	6 M
5	a	What are the Characteristics of Embedded System and discuss the types of embedded systems based on Generation.	6M
	b	Draw the Data Flow Model of ARM Processor and explain the same.	8M
	С	Mention the Differences between Microprocessor and Microcontroller.	6M
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